

Structural and Electronic Properties of InN Surfaces and Interfaces

L. Fishwick

Surface, Interface and Thin Film Group

Post-grad Seminar

12 February 2009



Introduction

Techniques

XPS

CAICISS

Future Research

The Highly Mismatched Compounds group: Academics:



Prof. Chris McConville
Supervisor



Dr. Tim Veal
EPSRC career
acceleration fellow

PhD students:

Mr. Philip D. C. King

3rd year

Ms. Louise R. Bailey

2nd year

Mr. Liam Fishwick

Mr. Wojciech Linhart

1st year

I also work closely with Dr. Marc Walker and Mr. Matthew Brown performing ion scattering experiments.



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A highly mismatched compound is compound with a distinct cation/anion size and electronegativity mismatch. The particular branch of HMC that is the focus of research in the group at warwick are SCAMS.

- SCAMS: Significantly Cation-Anion Mismatched Semiconductors. The cation is much larger and less electronegative than the anion, e.g. InN, ZnO, CdO.



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Indium nitride is a narrow band gap semiconductor with a band gap of ~ 0.64 eV.

- Exhibits an electron accumulation layer at the surface
- InGaN ternary alloy is known now to have a band gap spanning from the near IR for InN to the UV for GaN.
- Branch point energy is well above the conduction band minimum (~ 1.5 eV).

Mahboob *et al.*, Phys. Rev. Lett., **92**, 036804, 2004

King *et al.*, Phys. Rev. B., **77**, 045316, 2008



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Scandium nitride was initially thought to be a semi-metal, but after more careful calculation was found to be a semiconductor with a direct transition at the Γ point of ~ 2.1 eV.

- Interest in use as buffer layers in III-N compounds, e.g. GaN/InN.
- Demonstrates downwards band bending at the surface.
- May exhibit interesting electronic properties.

Lambrecht, Phys. Rev. B, **62**, 20, (2000)



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Important techniques for this project:

- X-ray photoelectron spectroscopy
- Co-axial impact collision ion scattering spectroscopy
- Low energy electron diffraction

Some complementary techniques that will also be utilised:

- Scanning electron microscopy
- Hall measurements



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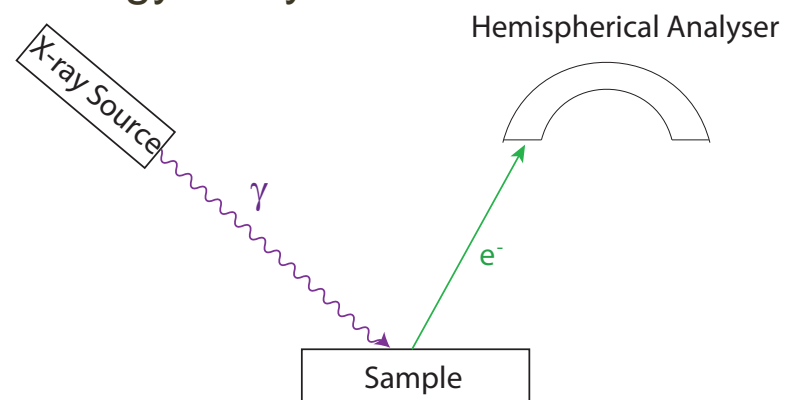
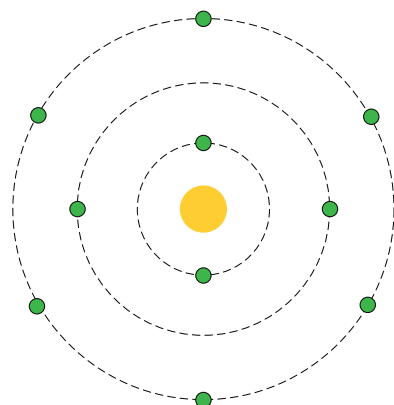
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An incident x-ray photon causes the ejection of a core level electron, which is then accelerated towards an electron energy analyser.

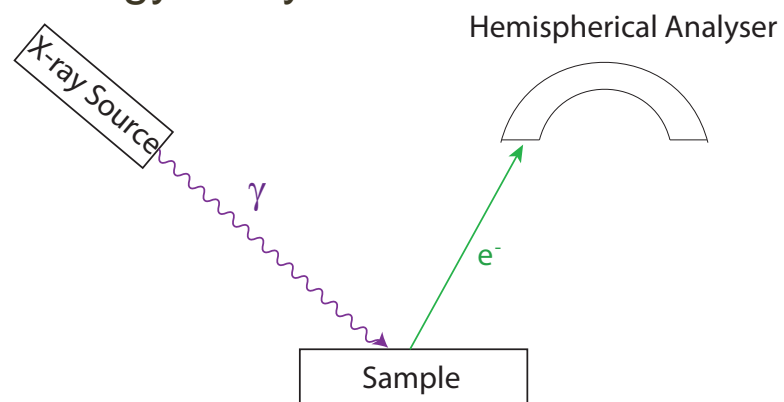
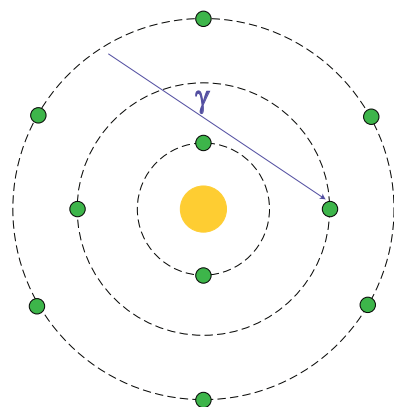


The binding energy of the detected electron is:

$$E_B = E_\gamma - E_k - \phi_{\text{analyser}}$$

Each element produces a characteristic set of peaks in the spectra at specific binding energies directly identifying that species (usually!)

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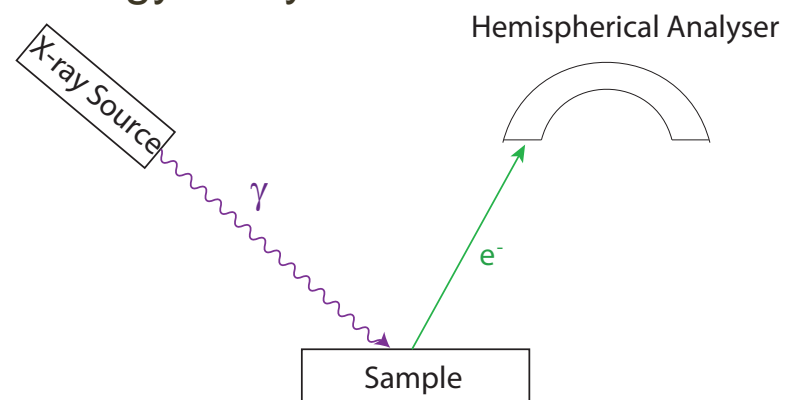
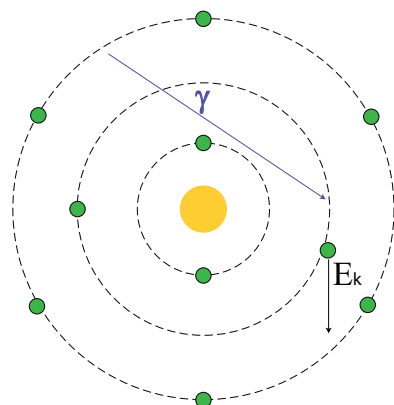


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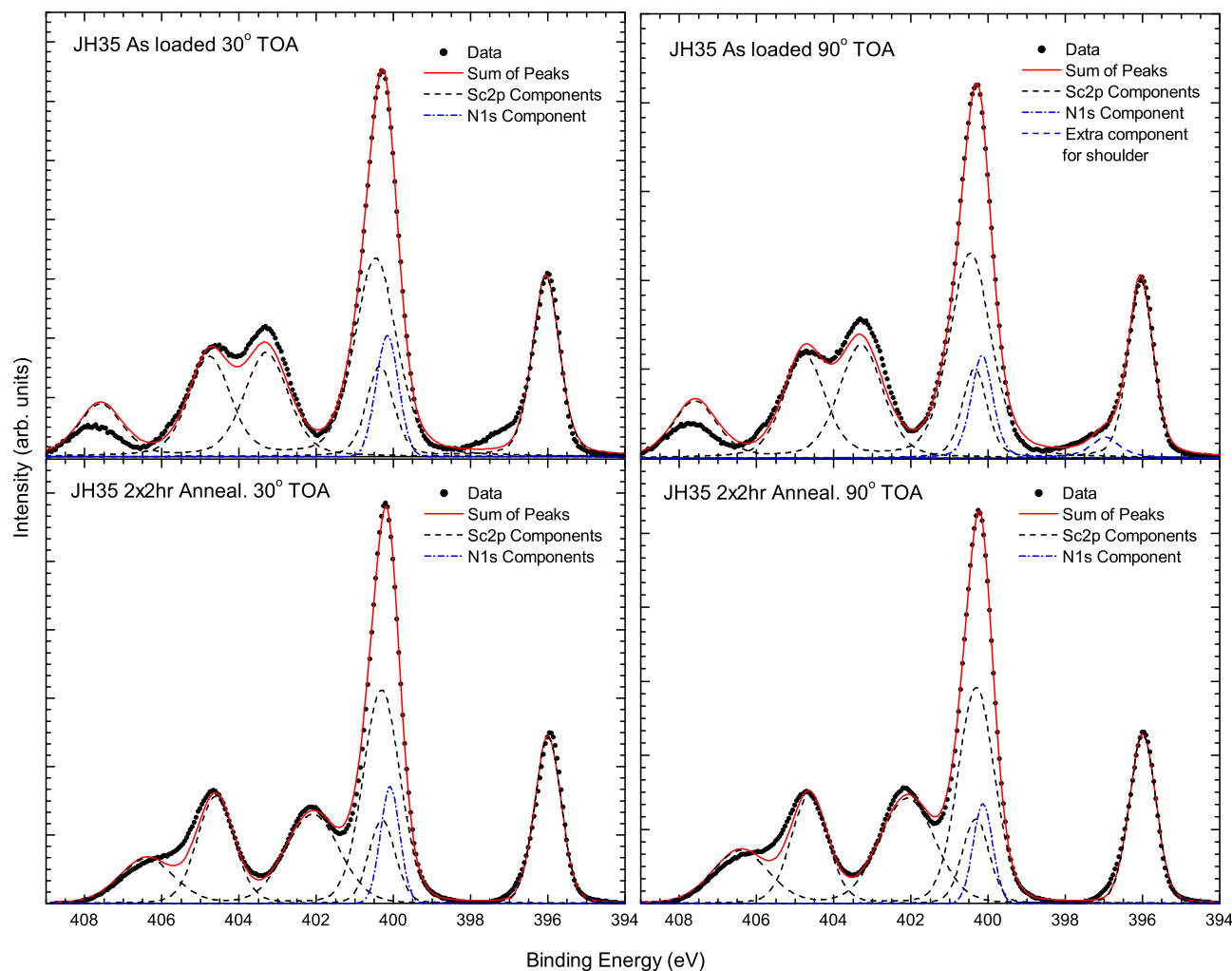


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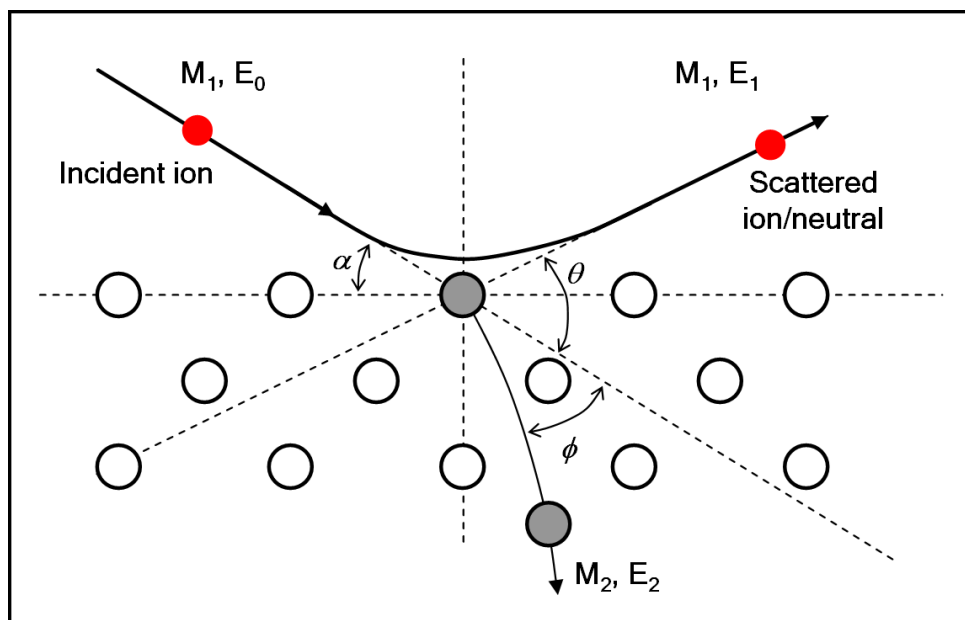
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Sample XPS spectra for a Sc2p region. Fitted for different surface preparations and take off angles.

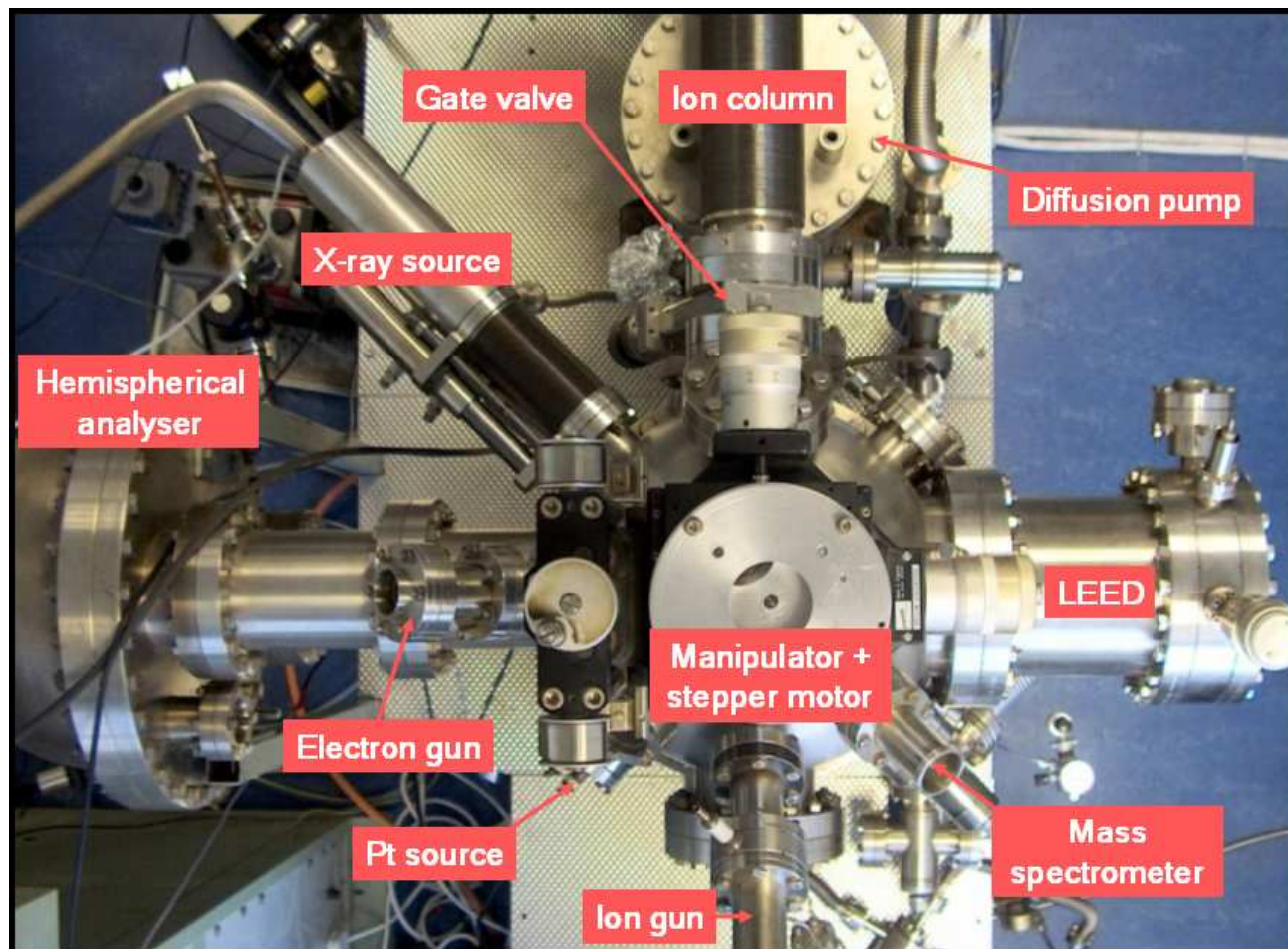


Ion scattering can be illustrated as a simple collision between hard spheres. Incident ions scatter off atoms in the near surface region.



CAICISS is a novel low energy ion scattering technique, where ions with incident energy of 1 – 5 keV are incident on the surface and 180° backscattering geometry is utilised for detection.

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At Warwick we have the only CAICISS chamber in the country.



The data is compared with simulations such as those created by the FAN package

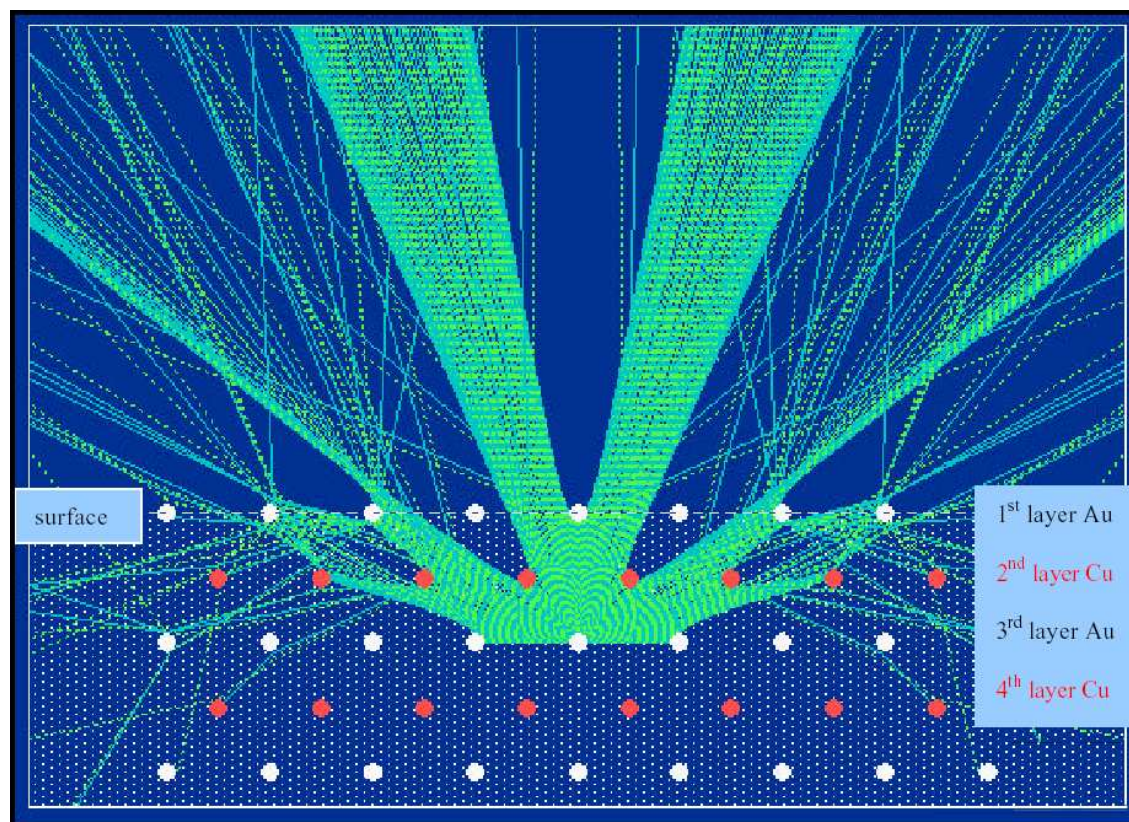


Figure 1: FAN trajectory cones from the near surface region of Au/Cu

Previous CAICISS work performed by the group has led to a model for wurtzite InN to be formed with In adlayers at the surface of In terminated InN.

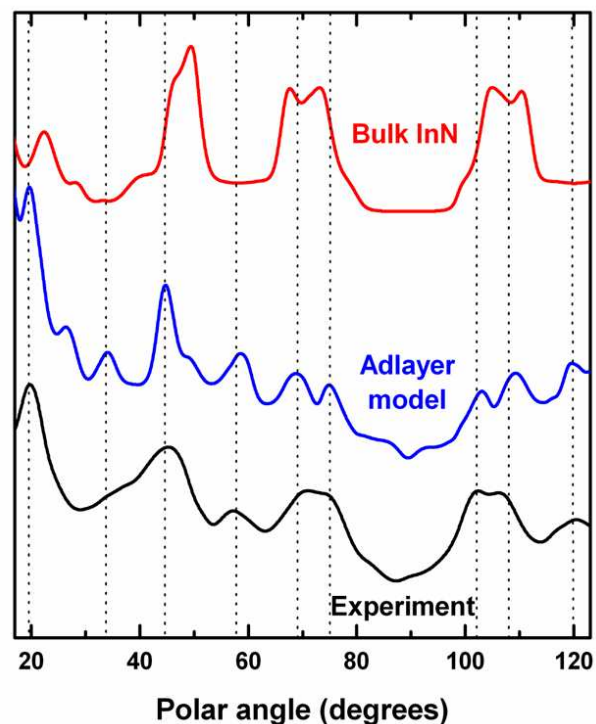


Figure 2: Idealised bulk terminated InN and In adlayer model shown with experimental result below

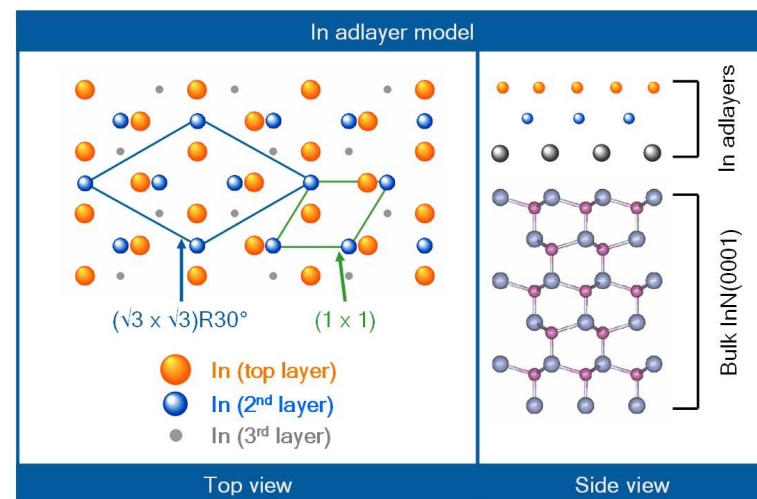


Figure 3: InN adlayer schematic, top view and side view shown

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- Further investigation into the structural and electronic properties of InN and ScN.
- Study other HMC's.
- Develop cleaning techniques for InN.



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Some issues faced when cleaning InN are:

- Low non-congruent temperature $\sim 450^{\circ}\text{C}$.
- Preferentially sputter N from surface.
- Weak material so cannot withstand Ar^{+} ion bombardment.

Need to develop cleaning methods that maintain both the electronic and structural properties of the surface, without introducing many defects. Currently atomic hydrogen cleaning is performed, however, hydrogen acts as a donor defect altering the electronic properties.

